



SEMI® International Standards Program

Compound Semiconductor Technical Committee Meeting

Room: Office “Staffelsee”
Internationales Congress Center München, Germany

***Thursday 12th Nov 2026,
11:15-13:00 CET***

V1 12.11.2026

Co-chairs:

- [Dr. Arnd-Dietrich Weber, SiCrystal](#)
- [Dr. Christian Kranert, IISB Fraunhofer](#)

European Compound Semiconductor Committee Meeting (Hybrid Meeting)

11:15	Welcome and Self-Introductions	all
11:20	SEMI Standards Overview and Legal Reminders	SEMI Staff
11:25	Review of the minutes and action items from the previous meeting	SEMI Staff
11:30	Task Force Reports (~5 minutes each) • SiC-Task Force (M81 Review) • 5-year Review Task Force (inactive) • Silicon Carbide Engineered Substrate Task Force (inactive) • Test Method for SiC -Task Force • SiC Epi Defects Task Force	A. Weber H.C. Alt E. Cela C. Kranert C. Kranert
11:55	Ballot Authorization • Doc. 7160 New Standard: Guide for Defects found in Homoepitaxial Layers of Silicon Carbide	C. Kranert
12:10	5y Review: Identify published documents due to 5y Review	A. Weber
12:20	Compound Materials Liaison Reports • North America • Japan • China	SEMI Staff
12:30	New Business: • Aluminium Nitride Wafer Specification (TFOF & SNARF) • Test Method Residual Stress 4H-SiC Wafers (SNARF) • Open Discussion	J. Grandusky C. Kranert N.N.
12:45	Any Other Business / Questions	A. Weber
12:50	Next Meeting	
12:55	End	